

# MGP19N35CL, MGB19N35CL

Preferred Device



ON Semiconductor™

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## Ignition IGBT 19 Amps, 350 Volts N-Channel TO-220 and D<sup>2</sup>PAK

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Over-Voltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

- Ideal for IGBT-On-Coil or Distributorless Ignition System Applications
- High Pulsed Current Capability up to 50 A
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage to Interface Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- Optional Gate Resistor (R<sub>G</sub>)

**MAXIMUM RATINGS** (-55°C ≤ T<sub>J</sub> ≤ 175°C unless otherwise noted)

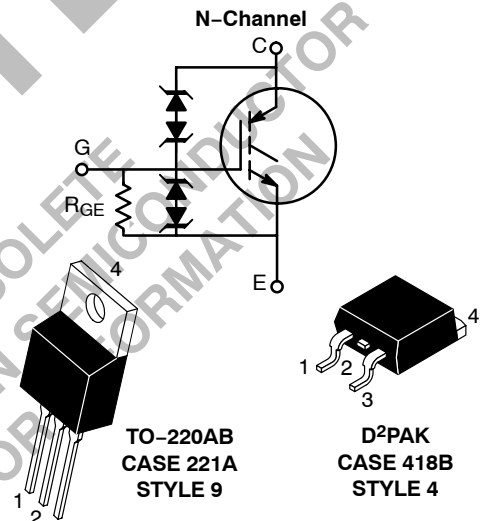
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CE(S)</sub>	380	V <sub>DC</sub>
Collector-Gate Voltage	V <sub>CER</sub>	380	V <sub>DC</sub>
Gate-Emitter Voltage	V <sub>GE</sub>	22	V <sub>DC</sub>
Collector Current - Continuous @ T <sub>C</sub> = 25°C - Pulsed	I <sub>C</sub>	19 50	A <sub>DC</sub> A <sub>AC</sub>
ESD (Human Body Model) R = 1500 Ω, C = 100 pF	ESD	8.0	kV
ESD (Machine Model) R = 0 Ω, C = 200 pF	ESD	800	V
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	165 1.1	Watts W/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C

### UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE

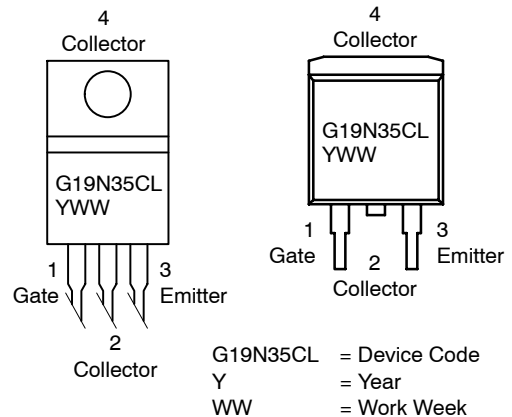
**CHARACTERISTICS** (-55°C ≤ T<sub>J</sub> ≤ 175°C)

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy V <sub>CC</sub> = 50 V, V <sub>GE</sub> = 5.0 V, Pk I <sub>L</sub> = 22.4 A, L = 2.0 mH, Starting T <sub>J</sub> = 25°C	E <sub>AS</sub>	500	mJ
V <sub>CC</sub> = 50 V, V <sub>GE</sub> = 5.0 V, Pk I <sub>L</sub> = 17.4 A, L = 2.0 mH, Starting T <sub>J</sub> = 150°C		300	
Reverse Avalanche Energy V <sub>CC</sub> = 100 V, V <sub>GE</sub> = 20 V, L = 3.0 mH, Pk I <sub>L</sub> = 25.8 A, Starting T <sub>J</sub> = 25°C	E <sub>AS(R)</sub>	1000	mJ

**19 AMPERES  
350 VOLTS (Clamped)  
V<sub>CE(on)</sub> @ 10 A = 1.8 V Max**



### MARKING DIAGRAMS & PIN ASSIGNMENTS



### ORDERING INFORMATION

Device	Package	Shipping
MGP19N35CL	TO-220	50 Units/Rail
MGB19N35CLT4	D2PAK	800 Tape & Reel

Preferred devices are recommended choices for future use and best overall value.

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## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.9	°C/W
Thermal Resistance, Junction to Ambient	TO-220 $R_{\theta JA}$	62.5	
	D <sup>2</sup> PAK (Note 1.) $R_{\theta JA}$	50	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	$T_L$	275	°C

## ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Clamp Voltage	$BV_{CES}$	$I_C = 2.0 \text{ mA}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	320	350	380	$V_{DC}$
			$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	330	360	380	
Zero Gate Voltage Collector Current	$I_{CES}$	$V_{CE} = 300 \text{ V},$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$	-	1.5	20	$\mu\text{A}_{DC}$
			$T_J = 150^\circ\text{C}$	-	15	40*	
			$T_J = -40^\circ\text{C}$	-	0.7	1.5	
Reverse Collector-Emitter Leakage Current	$I_{ECS}$	$V_{CE} = -24 \text{ V}$	$T_J = 25^\circ\text{C}$	-	0.35	1.0	mA
			$T_J = 150^\circ\text{C}$	-	10	20*	
			$T_J = -40^\circ\text{C}$	-	0.05	0.5	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75 \text{ mA}$	$T_J = 25^\circ\text{C}$	25	33	50	$V_{DC}$
			$T_J = 150^\circ\text{C}$	25	36	50	
			$T_J = -40^\circ\text{C}$	25	30	50	
Gate-Emitter Clamp Voltage	$BV_{GES}$	$I_G = 5.0 \text{ mA}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	17	20	22	$V_{DC}$
Gate-Emitter Leakage Current	$I_{GES}$	$V_{GE} = 10 \text{ V}$	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	384	500	1000	$\mu\text{A}_{DC}$
Gate Resistor (Optional)	$R_G$	-	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	-	70	-	$\Omega$
Gate Emitter Resistor	$R_{GE}$	-	$T_J = -40^\circ\text{C to } 150^\circ\text{C}$	10	20	26	k $\Omega$

### ON CHARACTERISTICS (Note 2.)

Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0 \text{ mA},$ $V_{GE} = V_{CE}$	$T_J = 25^\circ\text{C}$	1.4	1.7	2.0	$V_{DC}$
			$T_J = 150^\circ\text{C}$	0.75	1.1	1.4	
			$T_J = -40^\circ\text{C}$	1.6	1.9	2.1*	
Threshold Temperature Coefficient (Negative)	-	-	-	-	4.4	-	mV/°C

1. When surface mounted to an FR4 board using the minimum recommended pad size.

2. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

\*Maximum Value of Characteristic across Temperature Range.

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## ELECTRICAL CHARACTERISTICS (continued)

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
<b>ON CHARACTERISTICS (continued)</b> (Note 3.)							
Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 6.0 \text{ A}$ , $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.25	1.6	$V_{DC}$
			$T_J = 150^\circ\text{C}$	0.8	1.05	1.4	
			$T_J = -40^\circ\text{C}$	1.15	1.4	1.75*	
		$I_C = 10 \text{ A}$ , $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.2	1.5	1.8	
			$T_J = 150^\circ\text{C}$	1.0	1.3	1.6	
			$T_J = -40^\circ\text{C}$	1.3	1.6	1.9*	
		$I_C = 15 \text{ A}$ , $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.5	1.75	2.1	
			$T_J = 150^\circ\text{C}$	1.35	1.65	1.95	
			$T_J = -40^\circ\text{C}$	1.5	1.8	2.1*	
		$I_C = 20 \text{ A}$ , $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	1.7	2.0	2.3	
			$T_J = 150^\circ\text{C}$	1.6	1.9	2.2	
			$T_J = -40^\circ\text{C}$	1.7	2.0	2.3*	
$I_C = 25 \text{ A}$ , $V_{GE} = 4.0 \text{ V}$	$T_J = 25^\circ\text{C}$	2.0	2.25	2.6			
	$T_J = 150^\circ\text{C}$	2.0	2.3	2.7*			
	$T_J = -40^\circ\text{C}$	2.0	2.2	2.6			
Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 10 \text{ A}$ , $V_{GE} = 4.5 \text{ V}$	$T_J = 150^\circ\text{C}$	-	1.3	1.8	$V_{DC}$
Forward Transconductance	gfs	$V_{CE} = 5.0 \text{ V}$ , $I_C = 6.0 \text{ A}$	$T_J = -40^\circ\text{C}$ to $150^\circ\text{C}$	8.0	15	25	Mhos

## DYNAMIC CHARACTERISTICS

Input Capacitance	$C_{ISS}$	$V_{CC} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ $f = 1.0 \text{ MHz}$	$T_J = -40^\circ\text{C}$ to $150^\circ\text{C}$	-	1500	1800	pF
Output Capacitance	$C_{OSS}$			-	130	160	
Transfer Capacitance	$C_{RSS}$			-	6.0	8.0	

## SWITCHING CHARACTERISTICS (Note 3.)

Turn-Off Delay Time (Inductive)	$t_{d(off)}$	$V_{CC} = 300 \text{ V}$ , $I_C = 10 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$ , $L = 300 \mu\text{H}$	$T_J = 25^\circ\text{C}$	-	5.0	10	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	6.0	10	
Fall Time (Inductive)	$t_f$	$V_{CC} = 300 \text{ V}$ , $I_C = 10 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$ , $L = 300 \mu\text{H}$	$T_J = 25^\circ\text{C}$	-	6.0	10	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	11	15*	
Turn-Off Delay Time (Resistive)	$t_{d(off)}$	$V_{CC} = 300 \text{ V}$ , $I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$ , $R_L = 46 \Omega$	$T_J = 25^\circ\text{C}$	-	6.0	10	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	7.0	10	
Fall Time (Resistive)	$t_f$	$V_{CC} = 300 \text{ V}$ , $I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$ , $R_L = 46 \Omega$	$T_J = 25^\circ\text{C}$	-	12	20	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	18	22*	
Turn-On Delay Time	$t_{d(on)}$	$V_{CC} = 10 \text{ V}$ , $I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$ , $R_L = 1.5 \Omega$	$T_J = 25^\circ\text{C}$	-	1.5	2.0	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	1.5	2.0	
Rise Time	$t_r$	$V_{CC} = 10 \text{ V}$ , $I_C = 6.5 \text{ A}$ $R_G = 1.0 \text{ k}\Omega$ , $R_L = 1.5 \Omega$	$T_J = 25^\circ\text{C}$	-	4.0	6.0	$\mu\text{Sec}$
			$T_J = 150^\circ\text{C}$	-	5.0	6.0	

3. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

\*Maximum Value of Characteristic across Temperature Range.

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## TYPICAL ELECTRICAL CHARACTERISTICS (unless otherwise noted)

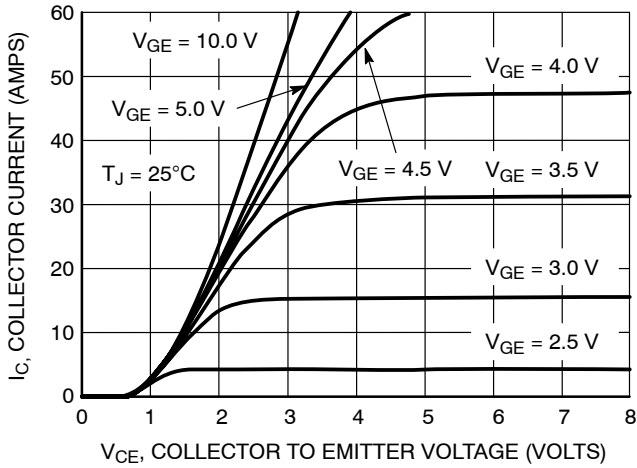


Figure 1. Output Characteristics

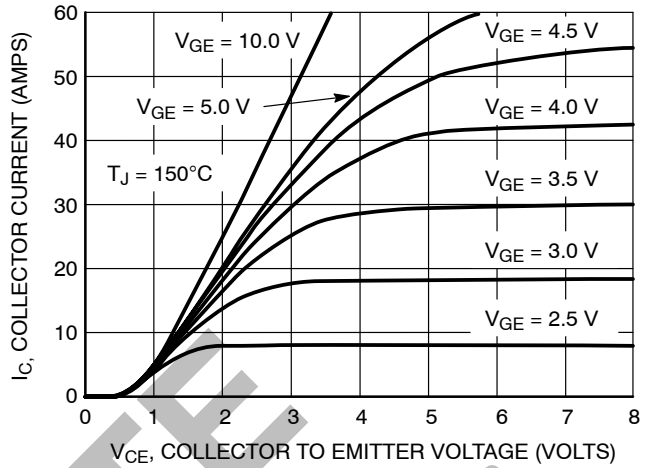


Figure 2. Output Characteristics

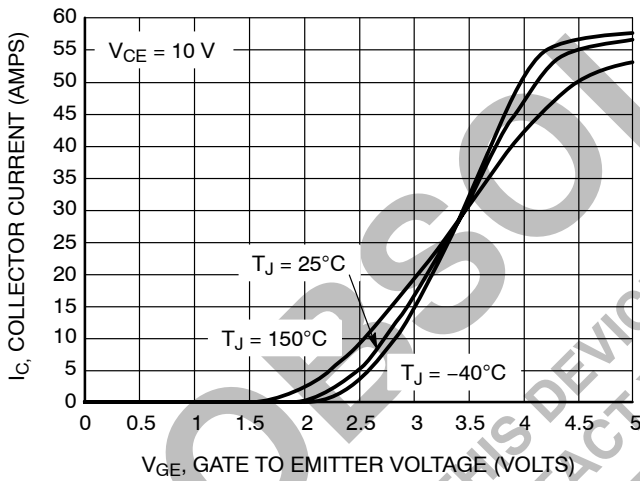


Figure 3. Transfer Characteristics

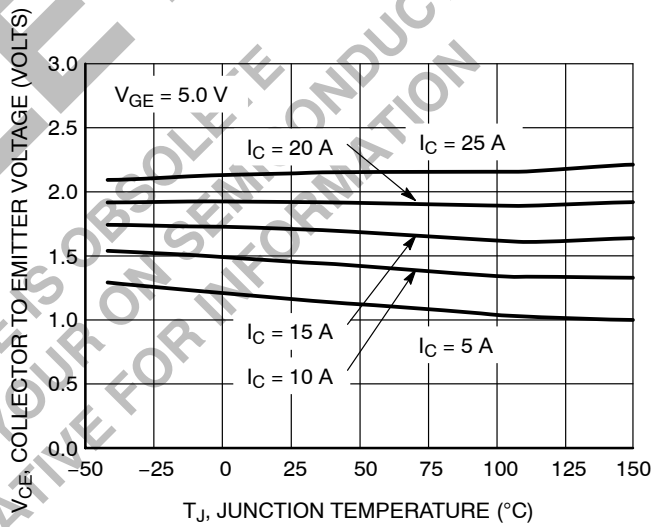


Figure 4. Collector-to-Emitter Saturation Voltage vs. Junction Temperature

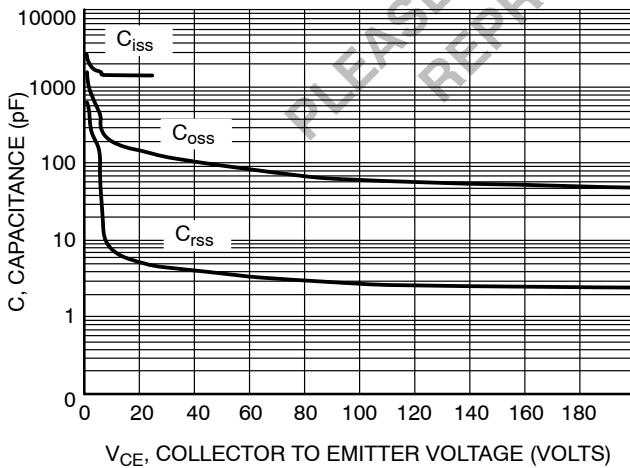


Figure 5. Capacitance Variation

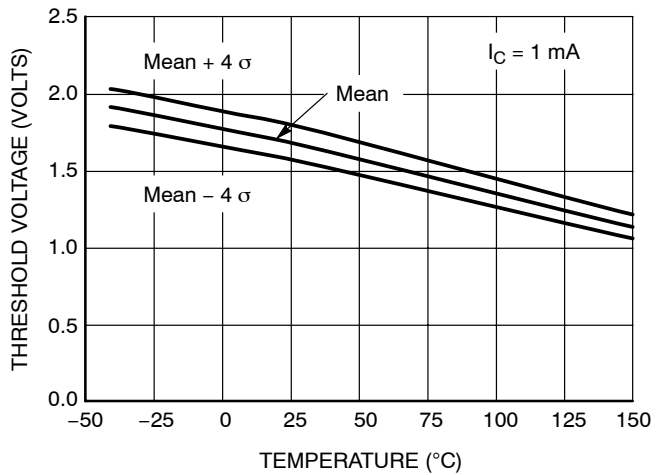
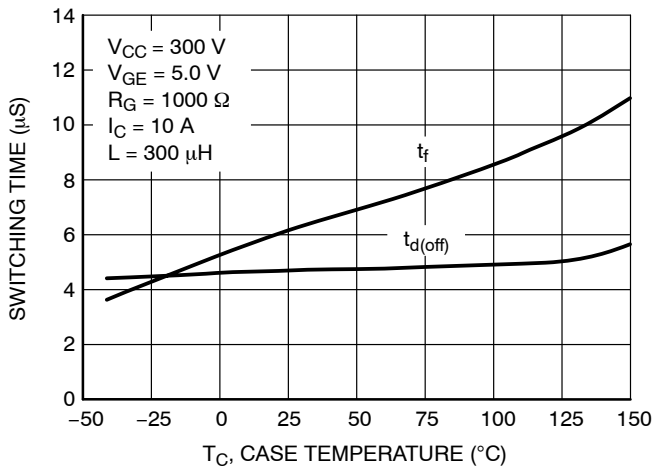
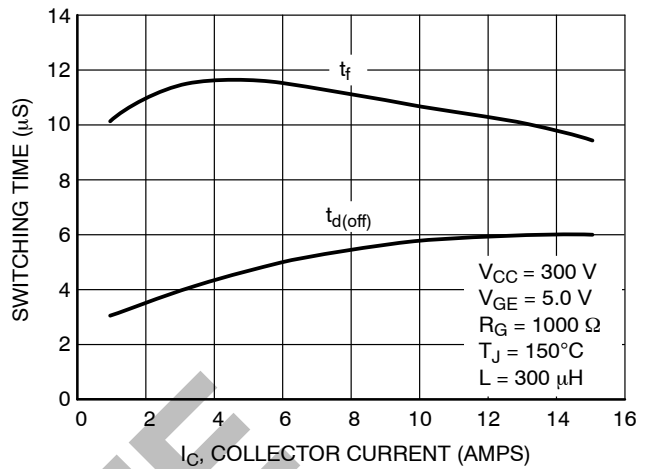


Figure 6. Threshold Voltage vs. Temperature

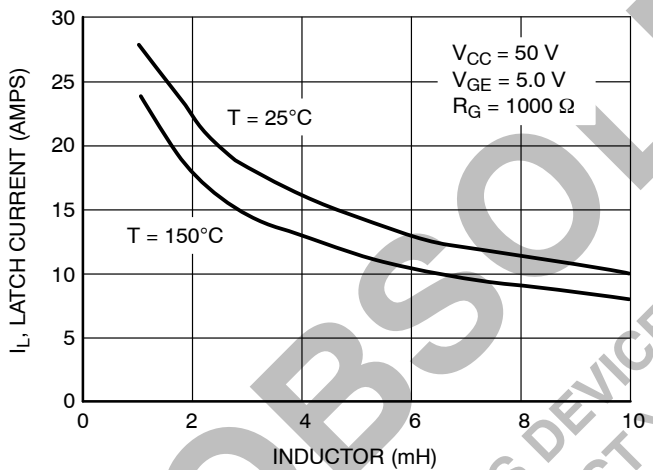
# MGP19N35CL, MGB19N35CL



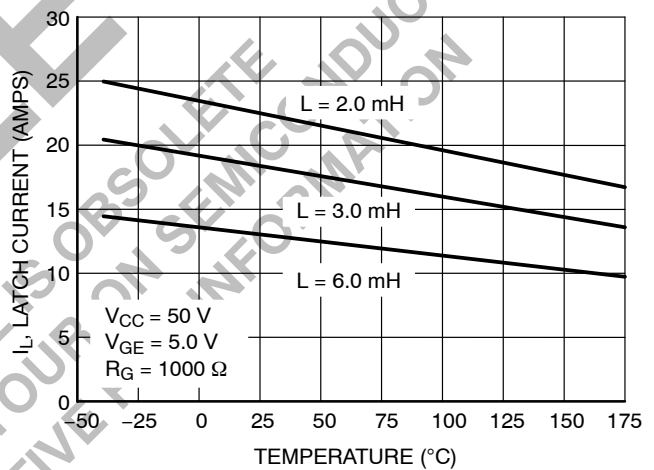
**Figure 7. Switching Speed vs. Case Temperature**



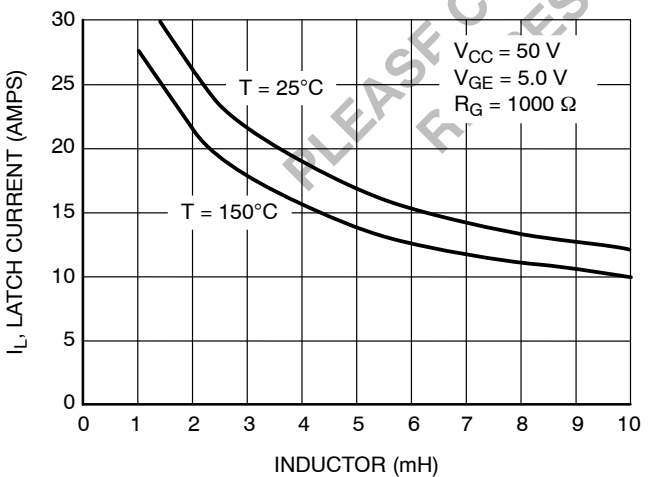
**Figure 8. Switching Speed vs. Collector Current**



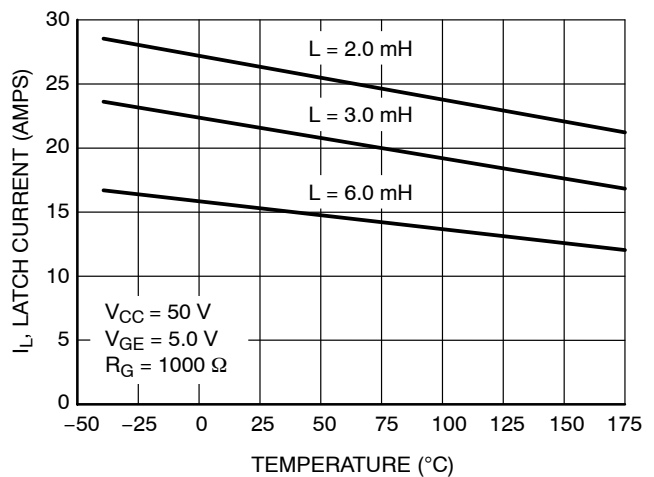
**Figure 9. Minimum Open Secondary Latch Current vs. Inductor**



**Figure 10. Minimum Open Secondary Latch Current vs. Temperature**



**Figure 11. Typical Open Secondary Latch vs. Inductor**



**Figure 12. Typical Open Secondary Latch vs. Temperature**

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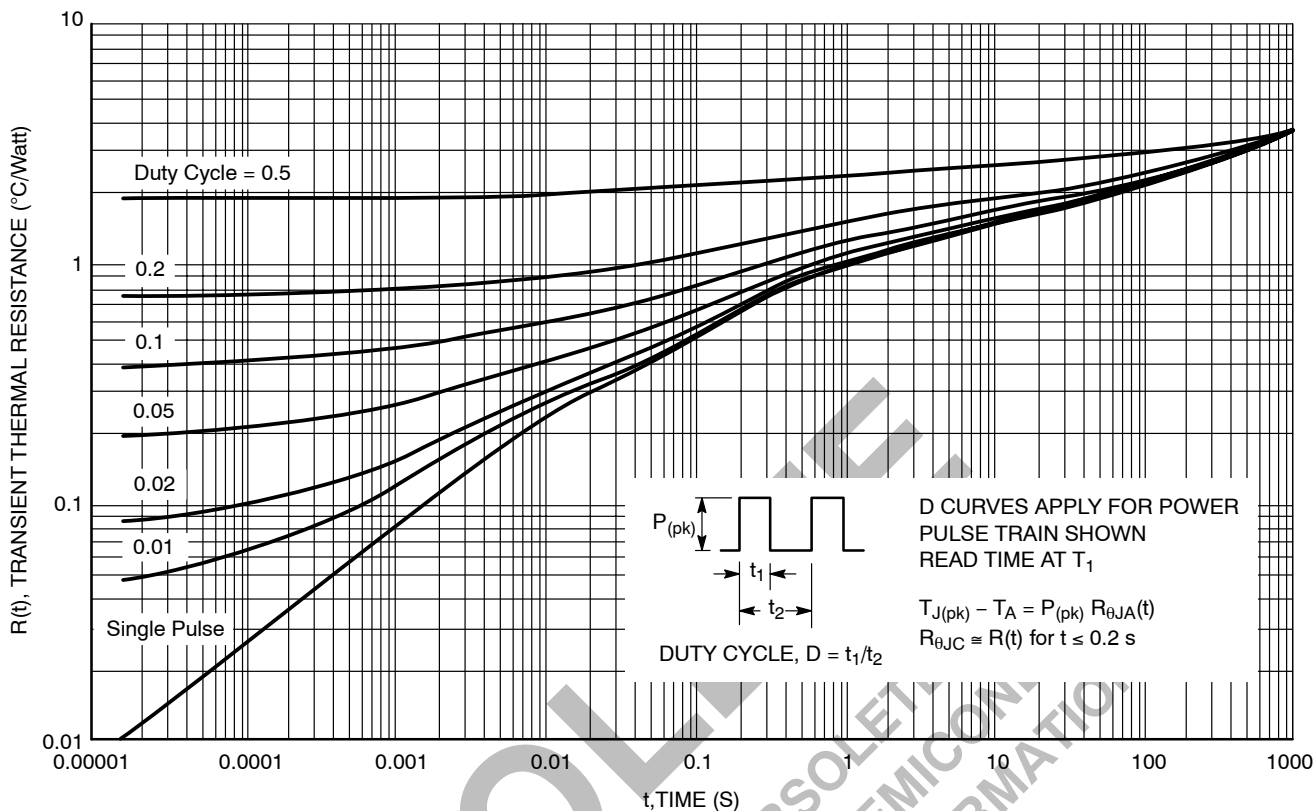


Figure 13. Transient Thermal Resistance (Non-normalized Junction-to-Ambient mounted on fixture in Figure 14)

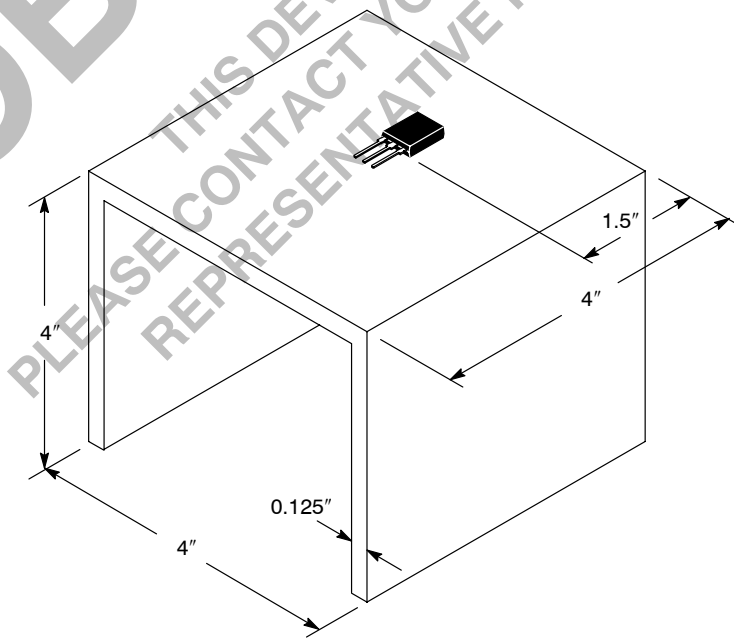


Figure 14. Test Fixture for Transient Thermal Curve (48 square inches of 1/8" thick aluminum)

MGP19N35CL, MGB19N35CL

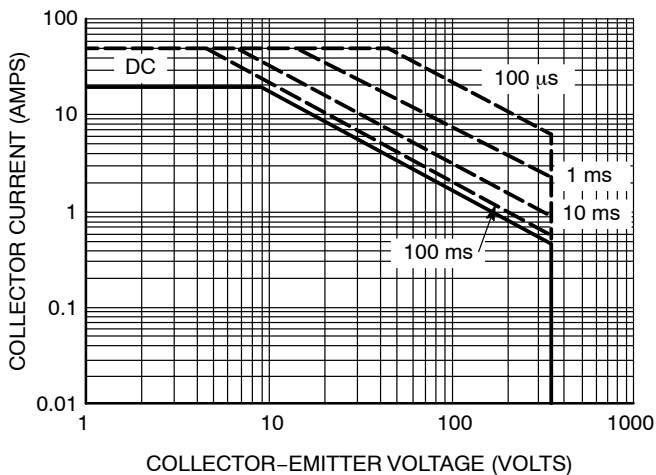


Figure 15. Single Pulse Safe Operating Area (Mounted on an Infinite Heatsink at  $T_C = 25^\circ\text{C}$ )

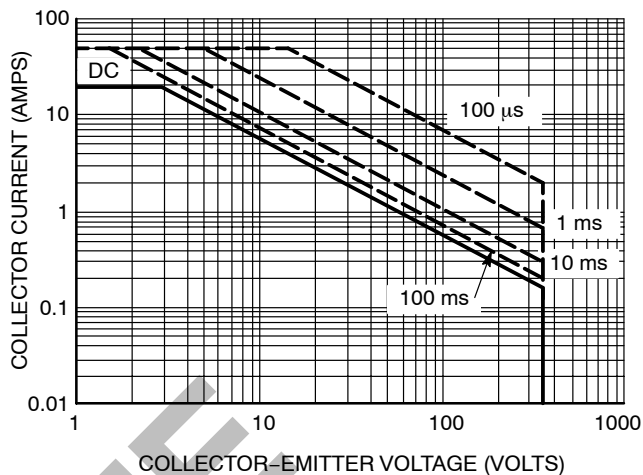


Figure 16. Single Pulse Safe Operating Area (Mounted on an Infinite Heatsink at  $T_C = 125^\circ\text{C}$ )

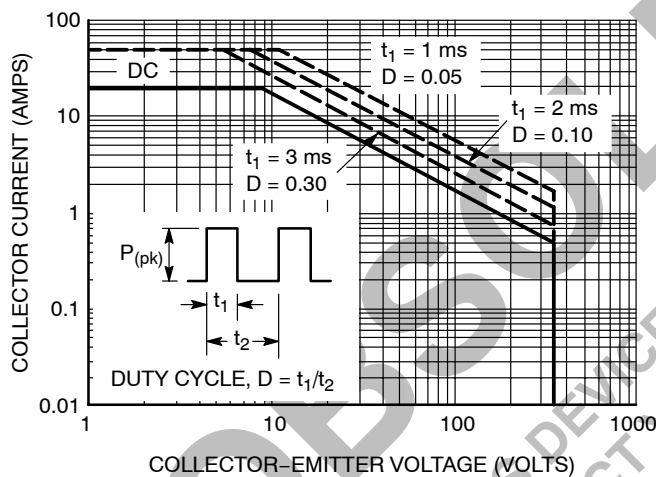


Figure 17. Pulse Train Safe Operating Area (Mounted on an Infinite Heatsink at  $T_C = 25^\circ\text{C}$ )

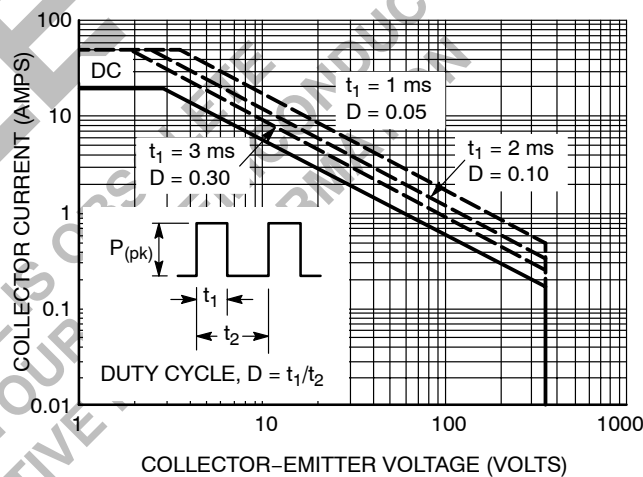
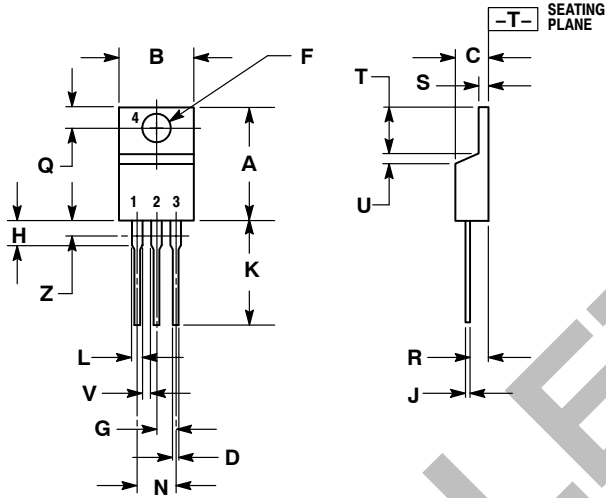


Figure 18. Pulse Train Safe Operating Area (Mounted on an Infinite Heatsink at  $T_C = 125^\circ\text{C}$ )

# MGP19N35CL, MGB19N35CL

## PACKAGE DIMENSIONS

TO-220 THREE-LEAD  
 TO-220AB  
 CASE 221A-09  
 ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.89	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 9:

- PIN 1. GATE
- COLLECTOR
- EMITTER
- COLLECTOR

OBSOLETE

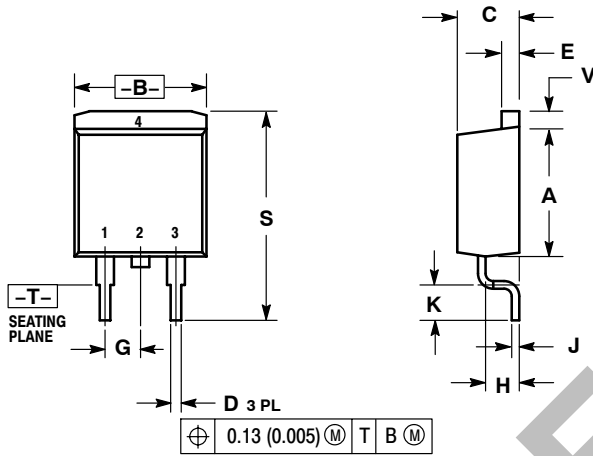
THIS DEVICE IS OBSOLETE  
 PLEASE CONTACT YOUR ON SEMICONDUCTOR  
 REPRESENTATIVE FOR INFORMATION



# MGP19N35CL, MGB19N35CL

## PACKAGE DIMENSIONS

D<sup>2</sup>PAK  
CASE 418B-03  
ISSUE D



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 4:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

OBSOLETE

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**Notes**

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**Notes**

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